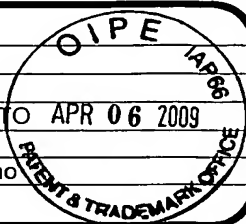


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Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT Date Submitted: April 6, 2009 <i>(use as many sheets as necessary)</i>				Complete if Known	
Sheet 1 of 1		Application Number 10/538,739 Filing Date 12/15/2003 First Named Inventor Yasuhiro OKAMOTO Art Unit 2814 Examiner Name Sarah Kate Salerno Attorney Docket Number 029437-0108			

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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		Country Code ³ Number ⁴ Kind Code ⁵ (if known)				
	C1	JP 2001-230263A	08-24-2001	NEC CORP.		A
	C2	JP 2000-353708A	12-19-2000	NEC CORP.		A
	C3	JP 09-027505	01-28-1997	NIPPONDENSO CO. LTD.		A
	C4	JP 08-083813	03-26-1996	MITSUBISHI ELECTRIC		A
	C5	JP 02-072667	03-12-1990	TOSHIBA CORP.		A

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
	C6	Shawn T. Bradley et al., "Influence of AlGaIn Deep Level Defects on AlGaIn/GaN 2-DEG Carrier Confinement," IEEE Transactions on Electron Devices, Vol. 48:3, March 2001, 7 pages.	
	C7	J. Li et al, "High Breakdown Voltage GaN HFET With Field Plate," Electronic Letters, February 1, 2001, Vol. 37:3, pp. 196-197.	

Examiner Signature	Date Considered
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